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(54) Title: PHOTOLITHOGRAPHY APPARATUS COMPRISING PROJECTION SYSTEM FOR CONTROL OF IMAGE SIZE

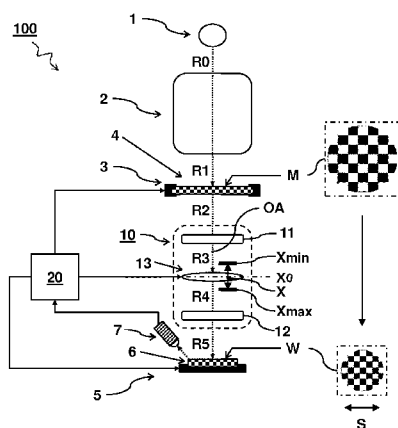


FIG 1A

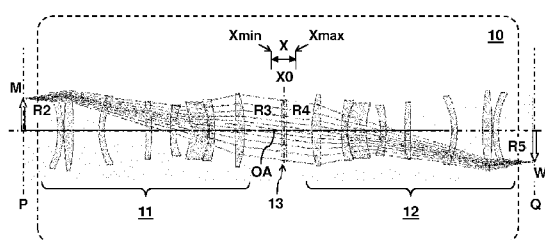


FIG 1B

(57) Abstract: The present disclosure concerns a photolithography apparatus (100) and method for controlling relative image size ($S1/S0$) of a projected substrate pattern (W). A projection system (10) is arranged for projecting an image of a mask pattern (M) as the substrate pattern (W) onto a substrate (6), wherein the projection system (10) comprises an adjustment lens (13) moveable in a range (X_{min}, X_{max}) encompassing a central position (X_0) for controlling a relative image size ($S1/S0$). The projection system (10) is arranged to project the mask pattern (M) onto the adjustment lens (13) such that, when the adjustment lens (13) is positioned at the central position (X_0), an apparent mask pattern (M') from a point of view of the adjustment lens (13) appears to be at a distance ($2 \cdot F$) from the adjustment lens (13) that is twice a focal length (F) of the adjustment lens (13).